

25. (amended) A positive-acting photoresist composition comprising:
- 1) a component that comprises photoacid-labile groups;
 - 2) a sulfonium photoacid generator compound that has an arylsulfonate, alicyclic sulfonate or acyclic sulfonate counter anion; and
 - 3) a non-hydroxylic solvent, and wherein the composition contains less than about 10 weight percent, based on total weight of the composition, of a hydroxylic solvent [is at least essentially free of a hydroxylic solvent].
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32. (amended) An article of manufacture comprising a substrate having coated thereon the photoresist composition of claim 25 [24].
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Please add the following new claims.

34. The article of claim 31, wherein the substrate is a microelectronic wafer.
35. The article of claim 32, wherein the substrate is a microelectronic wafer.
36. The article of claim 33, wherein the substrate is a microelectronic wafer.
37. A positive-acting photoresist composition comprising:
- 1) a component that comprises photoacid-labile groups;
 - 2) a sulfonium photoacid generator compound that is substituted with one or more of a moiety that has at least 2 carbon atoms and is selected from optionally substituted alkyl, optionally substituted alkenyl, optionally substituted alkynyl, optionally substituted substituted heteroalkyl, optionally substituted heteroalkenyl or optionally substituted hteroalkynyl; and
 - 3) a solvent of propylene glycol methyl ether acetate.

38. The photoresist composition of claim 37 wherein the composition contains less than about 10 weight percent, based on total weight of the composition, of a hydroxylic solvent.

39. The photoresist composition of claim 37 wherein the composition contains less than about 2 weight percent, based on total weight of the composition, of a hydroxylic solvent.

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40. A positive-acting photoresist composition comprising:
1) a component that comprises photoacid-labile groups;
2) a sulfonium photoacid generator compound that has an arylsulfonate, alicyclic sulfonate or acyclic sulfonate counter anion; and
3) a solvent of propylene glycol methyl ether acetate.

41. The photoresist composition of claim 40 wherein the composition contains less than about 10 weight percent, based on total weight of the composition, of a hydroxylic solvent.

42. The photoresist composition of claim 40 wherein the composition contains less than about 2 weight percent, based on total weight of the composition, of a hydroxylic solvent.

Please cancel without prejudice claims 27-30.

REMARKS

Claims 1, 25 and 32 have been amended, claims 34-42 have been added, and claims 27-30 have been cancelled without prejudice. No new matter has been added by virtue of the amendments. For instance, basis for the amendments of claims 1 and 25 appears e.g. at page 4, first paragraph and original claim 22 of the application. Support for new claims 34-36 appears e.g. at page 7, line 9 of the application. Support for new claims 37-42 appears e.g. in